

Amendments to the Specification:

Please replace the paragraph found beginning on page 4, line 19 and ending on page 5, line 2, with the following paragraph:

To achieve the object of the present invention, there are provided the steps of 1) hardening the stacked carbon/phenolic preform; 2) carbonizing the phenolic resin and heat processing it, while the temperature is risen below 2300°C; 3) infiltrating and sintering said hardened and carbonized preform by infiltrating it with the liquid metal silicon in the temperature between 1400°C and 1800°C; and 4) inducting the compound including SiO₂ to have gas phase in the temperature range of 1400°C ~ 1800°C (desirably, in the temperature exceeding 2300°C and more desirably, in the temperature near 2500°C) and ultra-high heat processing as forming the anti-oxidant layer on the surface of the compound.

Please replace the paragraph found at page 7, lines 2-10, with the following paragraph:

The present invention provides a One-Shot process including high temperature heat processing and infiltration of preform including carbon, a surface processing method for preventing reacting product from forming on surface of the material and high temperature heat processing period controlling shape changing, forming a 3D reticular structure controlling the chemical reaction of carbon fiber and liquid metal silicon, and extinguishing the non-reacted metal silicon remaining inside and forming the anti-oxidation coated layer on the surface using chemical vapour reaction (CVR), which is needed to in the manufacturing process of C/SiC composite.

Please replace the paragraph found at page 7, lines 11-18, with the following paragraph:

According to the present invention, the manufacturing process of C/SiC, which is used in order to increase the efficiency of missile ~~nozzle~~ nozzles, ~~engine~~ engines of ultrasonic ~~aeroplane~~ aeroplanes, ~~valve~~ valves used in high temperature ~~environment~~

environments, atomic power ~~plant~~ plants, can be simplified and the function of fire-resistance, oxide-resistance, and ~~structure~~ structural function are satisfied with the method according to the present invention. In addition, the producing period and cost can be greatly lowered ~~comparing~~ compared with the conventional method of chemical vapour infiltration (CVI). And the result of the thermal resistance test being described later shows that it has good reproducibility.

Please replace the paragraph found at page 11, lines 5-11, with the following paragraph:

This process covers step 9 in Figure 1. A 3D reticular structure is formed after the reaction is finished as shown in Figure 4. If the metal silicon becomes ~~to~~ silicon carbide by reacting with carbonized product, the volume is increased comparing with that of pre-sintering reaction, and stress caused by volume increasing can be applied to the air pore inside the product. Because of that, sufficient air pore should be made as 5~10% more than needed through heat processing before the infiltration of the metal silicon is performed.